

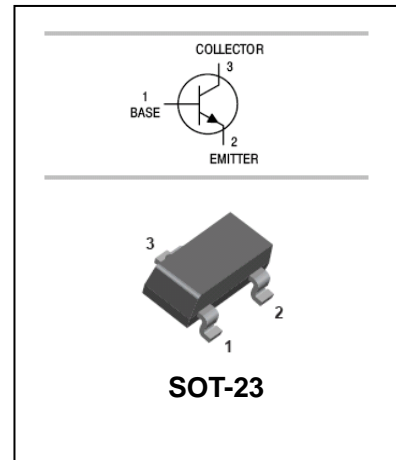


## Silicon Epitaxial Planar Transistor

## 2SC5344

### FEATURES

- High  $h_{FE}$
- Complementary pair with 2SA1981



### APPLICATIONS

- General small signal amplifier

### ORDERING INFORMATION

Type No.	Marking	Package Code
2SC5344	FAO/FAY	SOT-23

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	35	V
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	800	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$



**Silicon Epitaxial Planar Transistor**

**2SC5344**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=35V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=1V, I_C=100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.5	V
Transition frequency	$f_T$	$V_{CE}=5V, I_C=10mA$		120		MHz
Output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		13		pF

**CLASSIFICATION OF  $h_{FE}$**

Rank	O	Y
Range	100-200	160-320
Marking	FAO	FAY

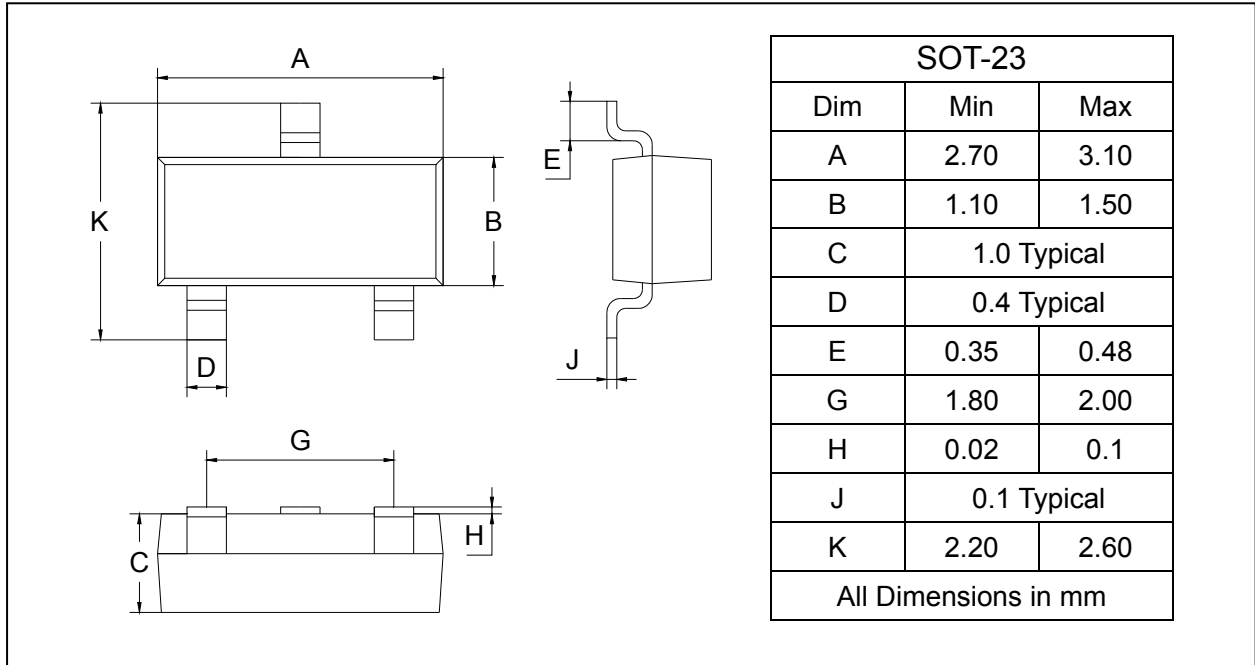
**Silicon Epitaxial Planar Transistor**

**2SC5344**

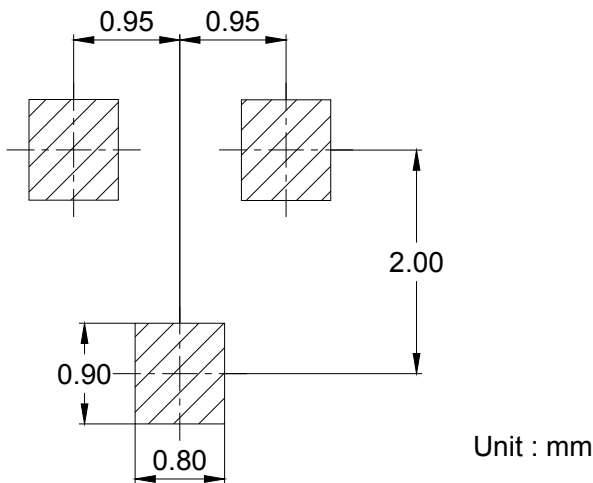
**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-23



**SOLDERING FOOTPRINT**



**PACKAGE INFORMATION**

Device	Package	Shipping
2SC5344	SOT-23	3000/Tape&Reel